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2N4851 thru 2N4853 (SILICON)

SILICON ANNULAR UNIJUNCTION TRANSISTORS

*MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
RMS Power Dissipation (1)	P_D	300	mW
RMS Emitter Current	I_e	50	mA
Peak-Pulse Emitter Current (2)	i_e	1.5	Amp
Emitter Reverse Voltage	V_{B2E}	30	Volts
Interbase Voltage (3)	V_{B2B1}	35	Volts
Operating Junction Temperature Range	T_J	-65 to +125	°C
Storage Temperature Range	T_{stg}	-65 to +200	°C

* Indicates JEDEC Registered Data
(1) Derate 3.0 mW/°C increase in ambient temperature.
(2) Duty cycle ≤ 1%, PRR = (see figure 6)
(3) Based upon power dissipation at T_A = 25°C

FIGURE 1 — UNIJUNCTION TRANSISTOR SYMBOL AND NOMENCLATURE

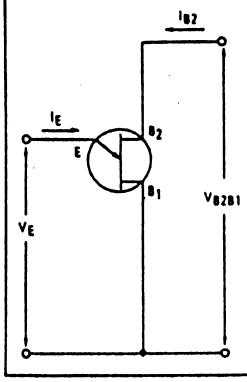
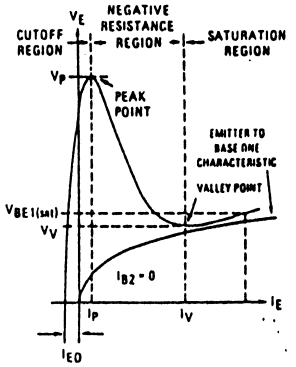


FIGURE 2 — STATIC EMITTER CHARACTERISTICS CURVES

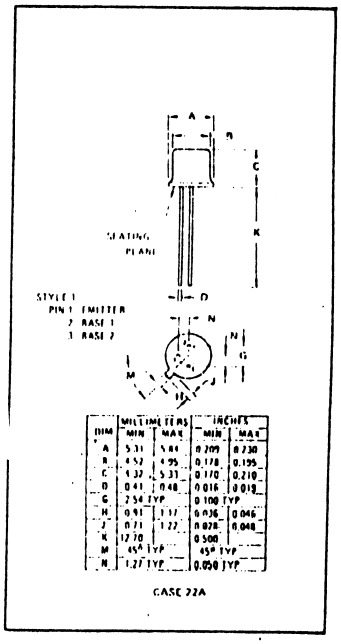


ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Rating	Figure No.	Symbol	Min	Typ	Max	Unit
*Intrinsic Standoff Ratio (1) (V_{B2B1} = 10 V) 2N4851 / 2N4852, 2N4853	4, 8	η	0.56 / 0.70	— / —	0.75 / 0.85	—
*Interbase Resistance (V_{B2B1} = 3.0 V, I_E = 0)	11, 12	r_{BB}	4.7	—	9.1	k ohms
*Interbase Resistance Temperature Coefficient (V_{B2B1} = 3.0 V, I_E = 0, T_A = -65 to +125°C)	12	α_{rBB}	0.2	—	0.8	%/°C
Emitter Saturation Voltage (2) (V_{B2B1} = 10 V, I_E = 50 mA)		$V_{EB1(sat)}$	—	2.5	—	Volts
Modulated Interbase Current (V_{B2B1} = 10 V, I_E = 50 mA)		$I_{B2(mod)}$	—	15	—	mA
*Emitter Reverse Current (V_{B2E} = 30 V, I_{B1} = 0) 2N4851, 2N4852 / 2N4853	7	I_{EB2O}	— / —	— / —	0.1 / 0.05	μA
*Peak-Point Emitter Current (V_{B2B1} = 25 V) 2N4851, 2N4852 / 2N4853	9, 10	I_P	— / —	— / —	2.0 / 0.4	μA
*Valley-Point Current (2) (V_{B2B1} = 20 V, R_{B2} = 100 ohms) 2N4851 / 2N4852 / 2N4853	13, 14	I_V	2.0 / 4.0 / 6.0	— / — / —	— / — / —	mA
*Base-One Peak Pulse Voltage 2N4851 / 2N4852 / 2N4853	3, 17	V_{OB1}	3.0 / 5.0 / 6.0	— / — / —	— / — / —	Volts
*Maximum Frequency of Oscillation	5	$f_{(max)}$	1.0	1.25	—	MHz

* Indicates JEDEC Registered Data.
(1) η, Intrinsic standoff ratio, is defined in terms of the peak-point voltage, V_P, by means of the equation: $V_P = \eta V_{B2B1} + V_F$, where V_F is about 0.49 volt at 25°C for I_P = 10 μA and decreases with temperature at about 2.5 mV/°C. The test circuit is shown in Figure 4. Components R_1, C_1, and the UJT form a relaxation oscillator; the remaining circuitry serves as a peak-voltage detector. The forward drop of Diode D_1 compensates for V_F. To use, the "cal" button is pushed, and R_2 is adjusted to make the current meter, M_1, read full scale. When the "cal" button is released, the value of η is read directly from the meter, if full scale on the meter reads 1.0.

(2) Use pulse techniques: PW = 300 μs, duty cycle ≤ 2.0% to avoid internal heating, which may result in erroneous readings.



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.31	5.84	0.209	0.230
B	4.52	4.95	0.178	0.195
C	4.32	5.33	0.170	0.210
D	0.41	0.48	0.016	0.019
G	2.54 TYP		0.100 TYP	
H	0.91	1.17	0.036	0.046
J	0.71	1.22	0.028	0.048
K	12.70		0.500	
M	45° TYP		45° TYP	
N	1.27 TYP		0.050 TYP	

FIGURE 3 — V_{OB1} TEST CIRCUIT

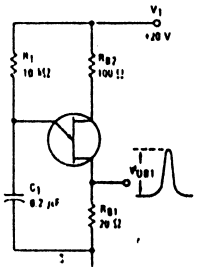


FIGURE 4 — η TEST CIRCUIT

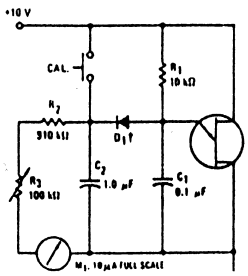


FIGURE 5 — $f_{(max)}$ TEST CIRCUIT

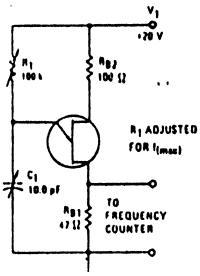
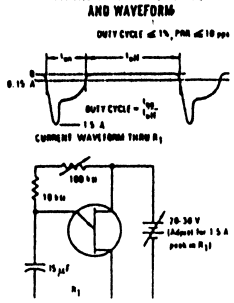



FIGURE 6 — PRR TEST CIRCUIT AND WAVEFORM